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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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Keep safety first in your circuit designs!

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HSM88WK

Silicon Schottky Barrier Diode for Balanced Mixer



ADE-208-049F (Z)

Rev. 6
Jul. 1998

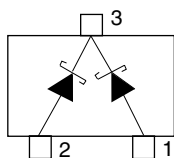
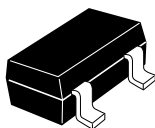
Features

- Proof against high voltage.
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSM88WK	C4	MPAK

Pin Arrangement



(Top View)

- 1 Anode
- 2 Anode
- 3 Cathode

HSM88WK

Absolute Maximum Ratings

(T_a = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V _R	10	V
Average rectified current	I _O ^{*1}	15	mA
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	–55 to +125	°C

Notes 1. Per one device

Electrical Characteristics^{*1}

(T_a = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V _{F1}	350	—	420	mV	I _F = 1 mA
	V _{F2}	500	—	580		I _F = 10 mA
Reverse current	I _{R1}	—	—	0.2	μA	V _R = 2V
	I _{R2}	—	—	10		V _R = 10V
Capacitance	C	—	—	0.85	pF	V _R = 0V, f = 1 MHz
Capacitance deviation	ΔC	—	—	0.10	pF	V _R = 0V, f = 1 MHz
Forward voltage deviation	ΔV _F	—	—	10	mV	I _F = 10 mA
ESD-Capability ^{*2}	—	30	—	—	V	C=200pF, Both forward and reverse direction 1 pulse.

Notes 1. Per one device

Notes 2. Failure criterion ; I_R ≥ 400nA at V_R = 2 V

Main Characteristic

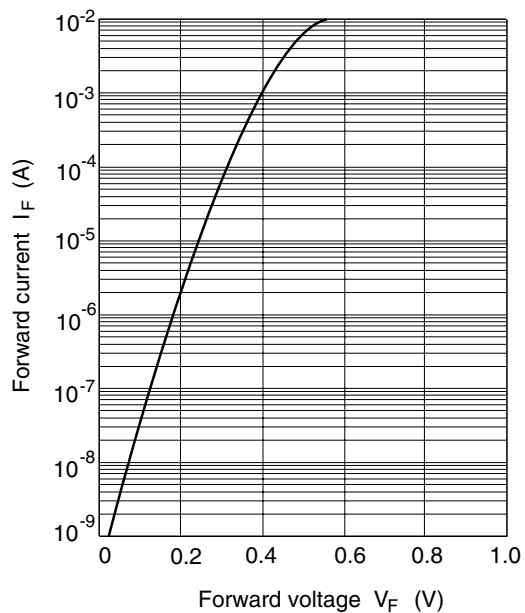


Fig.1 Forward current Vs. Forward voltage

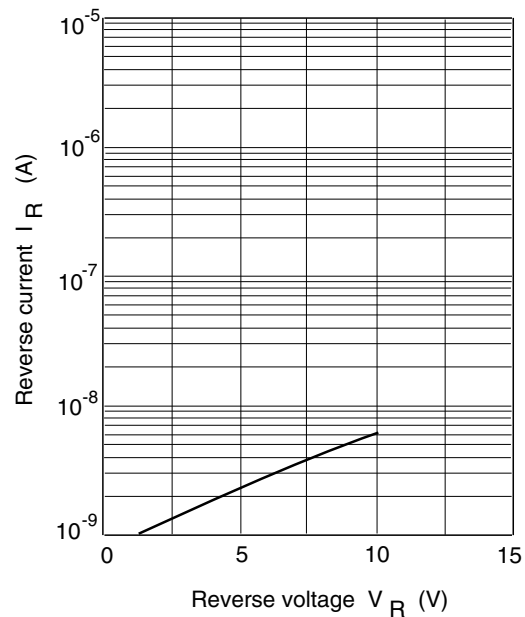


Fig.2 Reverse current Vs. Reverse voltage

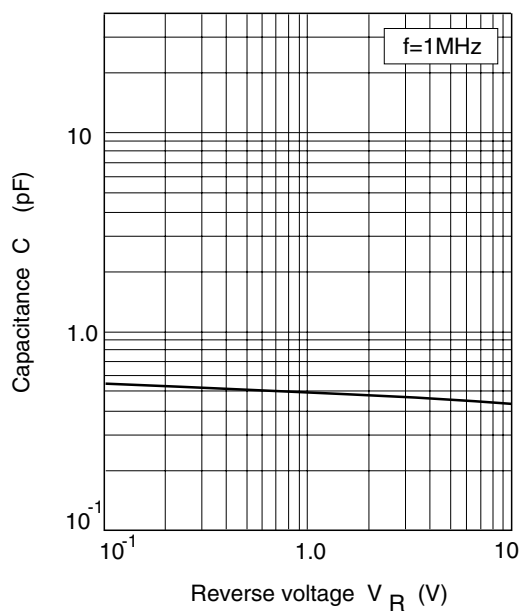
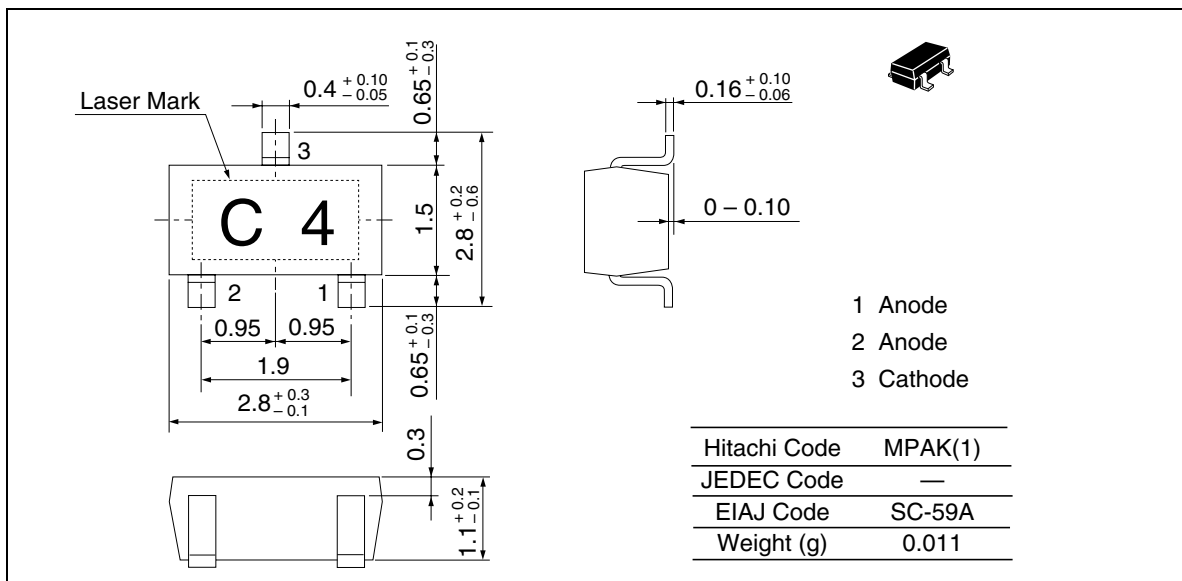


Fig.3 Capacitance Vs. Reverse voltage

HSM88WK

Package Dimensions

Unit : mm



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